

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Takuji MAEDA et al. Art Unit: 2876
Application No.: 10/553,725 Examiner: Hess, D.
Title: SEMICONDUCTOR MEMORY CARD, SEMICONDUCTOR MEMORY CONTROL
APPARATUS, AND SEMICONDUCTOR MEMORY CONTROL METHOD
International Application No.: PCT/JP2004/013703
International Filing Date : September 13, 2004
Priority Date : September 18, 2003
U.S. Filing Date : October 19, 2005

Mail Stop Amendment

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL LETTER

Sir:

In response to the Office Action dated March 11, 2009,
applicants hereby submit the enclosed papers including an
Amendment under 37 CFR 1.111.

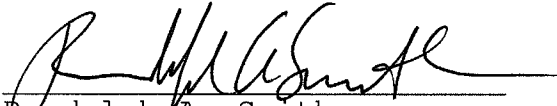
The required fees are calculated below:

Total Claims	<u>3</u>	-	<u>23</u>	=	<u>0</u>	\$0.00
Independent	<u>3</u>	-	<u>12</u>	=	<u>0</u>	\$0.00
TOTAL FEE DUE:						<u>\$0.00</u>

THE COMMISSIONER IS AUTHORIZED TO CHARGE THIS FEE AND ANY OTHER
FEES WHICH MAY BE REQUIRED OR CREDIT ANY OVERPAYMENT TO DEPOSIT
ACCOUNT NO. 19-2586, REFERENCING ATTORNEY DOCKET NO. 0074/057001.
THIS IS A GENERAL AUTHORIZATION EXCLUDING ONLY PAYMENT OF THE
ISSUE FEE.

Respectfully submitted,

Date: June 5, 2009


Randolph A. Smith
Reg. No. 32,548

SMITH PATENT OFFICE

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AMENDMENT UNDER 37 CFR 1.111

Sir:

In response to the Office Action dated March 11, 2009,
please amend the application as follows:

Amendments to the Claims begin on page 2 of this paper.

Remarks begin on page 6 of this paper.